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Supporting Information

Efficient Solar Cells with Enhanced Humidity and Heat Stability Based on Benzylammonium-caesium-formamidinium Mixed-Dimensional Perovskites

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Experimental Section

Preparation of perovskite precursor

 $HC(NH_2)_2I$ (FAI) and $HC(NH_2)_2Br$ (FABr) synthesis: FAI and FABr were prepared by dissolving formamidine acetate (98%, Sinopharm) in the excess of hydroiodic acid (HI, 57 wt% in H₂O, sigmaaldrich) and hydrobromic acid (HBr, 47 wt% in H₂O, sigma-aldrich) in a flask, respectively. After addition of HI or HBr, the solution was stirred at 0 °C for about 2 h. By rotary evaporation for 2 h at 60 °C, two white powders were obtained, respectively. After drying, the powders were recrystallized in diethyl ether. Finally, the purified FAI and FABr were gained by drying in a vacuum oven at 60 °C. $C_6H_5CH_2NH_3I$ (BEI) synthesis: BEI was obtained by reacting hydroiodic acid (HI, 57 wt%) with benzylamine (BE, 98.5%, Sinopharm) for about 1 h, the other preparation steps were same as the above.

Preparation of MD perovskite precursor solution: The $[(BE_2PbI_4)_x(FA_{0.9}Cs_{0.1}PbI_3)_{1-}]$ $x_{0.85}$ (FAPbBr₃)_{0.15} precursor solutions (1.35 M Pb²⁺) were obtained by dissolving corresponding lead iodide (PbI2, TCI), lead bromide (PbBr2, TCI), FAI, FABr, BEI and caesium iodide (CsI, Alfa) in mixed solvent of anhydrous methyl sulfoxide (DMSO, Sinopharm) and anhydrous N,Ndimethylformamide (DMF, Sinopharm) (DMSO:DMF=1:4 by volume) with stoichiometrically. MAPbI₃ perovskite solution (1.35 M Pb²⁺) was composed of corresponding lead iodide (PbI₂, TCI) and methylammonium iodide CH₃NH₃I (MAI, ≥99.5%, Xi'an p-OLED Corp.) in mixed solvent of anhydrous methyl sulfoxide (DMSO, Sinopharm) and anhydrous N, N-dimethylformamide (DMF, Sinopharm) (DMSO: DMF=4:1 by volume). Then, all the solutions were stirred for 1 h at 65 °C and filtered using 0.45 µm PVDF filters before film deposition.

Device fabrication: All of the perovskite devices were deposited on pretreated FTO substrate. The

compact layer of TiO₂ was coated by a spray pyrolysis method at 430 °C. The solution was gained by mixing the bis(acetylacetonate) (0.4 mL, Sinopharm, 99%) and titanium diisopropoxide (0.6 mL, Aldrich, 97%) in anhydrous isopropanol (7 mL, Sinopharm, 99.7%). Then, the mesoporous layer of TiO₂ was deposited by spin-coating the TiO₂ paste (30 nm, Dyesol, TiO₂: anhydrous ethanol =1:5.5 by weight) at 4000 r.p.m for 20 s and heated at 500 °C for 30 min. The perovskite layers were spin-coated on the mesoporous layer in the glovebox at 1100 r.p.m for 10 s and 4600 r.p.m for 35 s. Chlorobenzene (120 μ L) was drop-added on the surface during the spin coating step 15 s before the end. Then, the substrate should be annealed for 50 min at 105 °C. The HTM solution, composing of 73-mg spiro-OMeTAD, 29- μ L 4-tert-butylpyridine, 17- μ L Li⁺ salt and 8- μ L cobalt(III) salt in 1-mL chlorobenzene, was then spin-coated on the perovskite at 3000 r.p.m for 20 s. Finally, about 65-nm Au electrode was thermally evaporated under high vacuum.

Characterizations: XRD patterns were characterized using a Smartlab 9KW with the 2 θ range from 5° to 50°. SEM images were recorded on a high-resolution field-emission scanning electron microscope (FE-SEM, sirion200, FEI Corp., Holland). Ultraviolet-visible absorption spectra were characterized by ultraviolet–vis (UV–vis) spectrophotometer (U-3900H, HITACHI, Japan) with the measurement from 300 nm to 900 nm. Steady-state Photoluminescence (PL) spectra were measured by the spectrofluorometer (photon technology international). They were analyzed by a software Fluorescence. The samples were excited with a standard 450 W xenon CW lamp with an exciting wavelength of 473 nm. *J–V* curves were measured by a solar simulator (Newport, Oriel Class A, 91195A) at 100 mW/cm² illumination AM 1.5G with an active area of 0.09 cm². The scan rate is 50 mV s⁻¹. The source meter is Keithley 2420. Incident photon to current conversion efficiency (IPCE) spectra (300 nm to 900 nm) were executed on dual Xenon/quartz halogen light source (PV

Measurements, Inc.) in DC mode without bias light. Transient absorption (TA) were performed by the spectra LKS (Applied photophysics). The laser energy was $150 \,\mu$ J/cm² with a repetition rate of 5 Hz. The samples were tested under a 760-nm probe light wavelength and a 500-nm laser light wavelength. The construction of sample is glass/perovskite film.

Stability test: The perovskite devices were placed in a containers with $50\pm5\%$ RH to measure the humidity stability at room temperature in dark. Heat stability measurement was executed in a container at 85 °C in dark. All perovskite devices were aged under the same conditions.

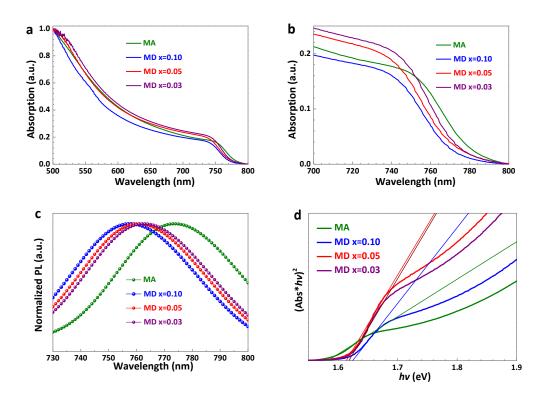


Fig. S1. (a) Normalized UV-vis absorption spectra, (b) partially enlarged normalized UV-vis absorption spectra and (c) partially enlarged normalized PL spectra of MAPbI₃ and $[(BE_2PbI_4)_x(FA_{0.9}Cs_{0.1}PbI_3)_{1-x}]_{0.85}(FAPbBr_3)_{0.15}$ (x=0.03, 0.05, 0.10) thin films. (d) Tauc plot from the UV-vis spectra of MAPbI₃ and $[(BE_2PbI_4)_x(FA_{0.9}Cs_{0.1}PbI_3)_{1-x}]_{0.85}(FAPbBr_3)_{0.15}$ (x=0.03, 0.05, 0.10) thin films. (d) Tauc plot from the UV-vis spectra of MAPbI₃ and $[(BE_2PbI_4)_x(FA_{0.9}Cs_{0.1}PbI_3)_{1-x}]_{0.85}(FAPbBr_3)_{0.15}$ (x=0.03, 0.05, 0.10) films.

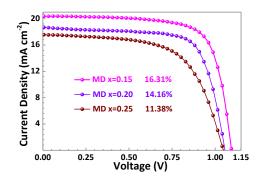


Fig. S2. *J*-*V* curves of [(BE₂PbI₄)_x(FA_{0.9}Cs_{0.1}PbI₃)_{1-x}]_{0.85}(FAPbBr₃)_{0.15} (x=0.15, 0.20, 0.25) PSCs.

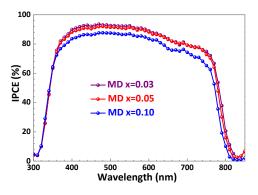


Fig. S3. IPCE spectra of the MD (x=0.03, 0.05 and 0.10) perovskite devices.

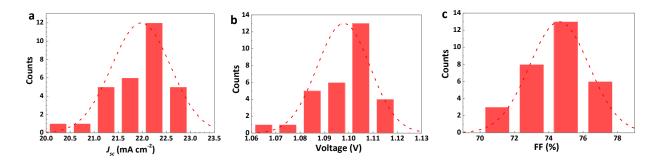


Fig. S4. (a) Short-circuit current density (J_{sc}), (b) Open circuit voltages (V_{oc}) and (c) Fill factor (FF) histogram fitted with a Gaussian distribution of the MD (x=0.05) perovskite devices over 30 measured devices.

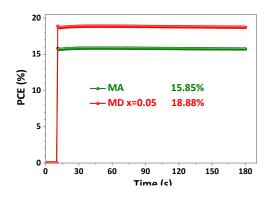


Fig. S5. Stabilized power output at maximum power point as a function of time for the best performing MAPbI₃ and MD (x=0.05) devices.

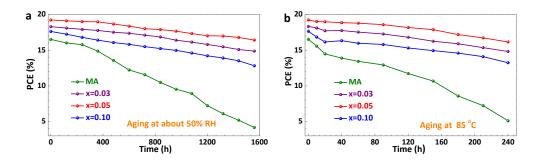
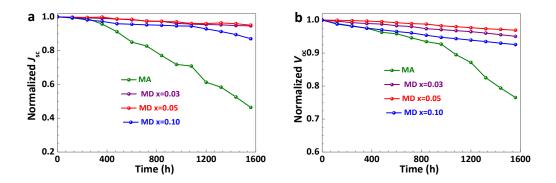


Fig. S6. PCE variation curves of unsealed MAPbI₃ and $[(BE_2PbI_4)_x(FA_{0.9}Cs_{0.1}PbI_3)_{1-x}]_{0.85}(FAPbBr_3)_{0.15}$ (x=0.03, 0.05, 0.10) perovskite devices when exposing to (a) 50% RH for 1600 h and (b) 85 °C for 240 h.



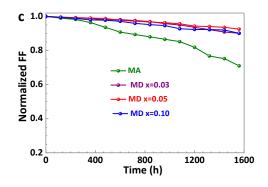


Fig. S7. Normalized (a) short-circuit current density (J_{sc}), (b) open circuit voltages (V_{oc}) and (c) fill factor (FF) variation curves of unsealed MAPbI₃ and [(BE₂PbI₄)_x(FA_{0.9}Cs_{0.1}PbI₃)_{1-x}]_{0.85}(FAPbBr₃)_{0.15} (x=0.03, 0.05, 0.10) perovskite devices under about 50% RH.

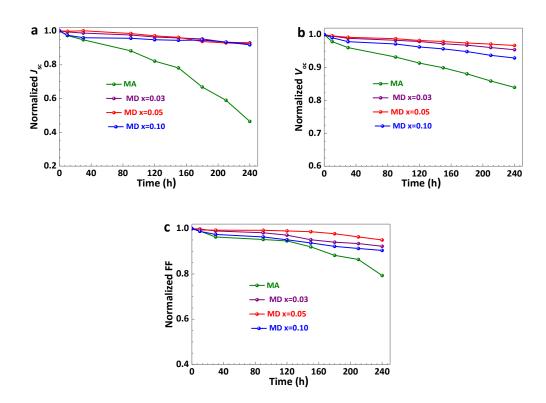


Fig. S8. Normalized (a) short-circuit current density (J_{sc}), (b) open circuit voltages (V_{oc}) and (c) fill factor (FF) variation curves of unsealed MAPbI₃ and [(BE₂PbI₄)_x(FA_{0.9}Cs_{0.1}PbI₃)_{1-x}]_{0.85}(FAPbBr₃)_{0.15} (x=0.03, 0.05, 0.10) perovskite devices at 85 °C.

Table S1. Photovoltaic parameters of the MAPbI₃ and the MD (x=0.05) perovskite devices under reverse and forward scan directions.

Device	$J_{\rm sc}$ (mA cm ⁻²)	$V_{\rm oc}$ (V)	FF (%)	PCE (%)
MA-Reverse	21.49	1.07	71.67	16.53
MA-Forward	20.18	1.07	68.74	14.86
MD-Reverse	22.79	1.10	76.74	19.24
MD-Forward	22.38	1.10	75.80	18.69

Table S2. Photovoltaic parameters of $[(BE_2PbI_4)_x(FA_{0.9}Cs_{0.1}PbI_3)_{1-x}]_{0.85}(FAPbBr_3)_{0.15}$ (x=0.15, 0.20, 0.25) PSC-

0.25) PSCs	•
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Device	$J_{\rm sc}$ (mA cm ⁻²)	$V_{ m oc}$ (V)	FF (%)	PCE (%)
x=0.15	20.38	1.10	73.07	16.31
x=0.20	18.69	1.06	71.67	14.16
x=0.25	17.55	1.05	61.94	11.38

Table S3. Photovoltaic parameters of [(BE₂PbI₄)_x(FA_{0.9}Cs_{0.1}PbI₃)_{1-x}]_{0.85}(FAPbBr₃)_{0.15} (x=0.15, 0.20,

0.25) PSCs f	for humidity st	ability measurements	under about 50% RH.

MAPbI ₃	$J_{\rm sc}$ (mA cm ⁻²)	$V_{ m oc}$ (V)	FF (%)	PCE (%)
0 h	21.49	1.07	71.67	16.51
120 h	21.33	1.06	70.96	16.02

240 h	21.27	1.05	70.39	15.79
360 h	20.57	1.05	69.09	14.87
480 h	19.59	1.03	67.09	13.58
600 h	18.27	1.03	65.08	12.23
720 h	17.78	1.02	64.08	11.57
840 h	16.58	1.00	63.08	10.49
960 h	15.44	0.99	62.07	9.53
1080 h	15.23	0.96	61.07	8.94
1200 h	13.17	0.93	58.70	7.23
1320 h	12.55	0.89	55.01	6.11
1440 h	11.30	0.85	53.94	5.19
1560 h	9.97	0.82	50.90	4.17
MD (x=0.03)	$J_{\rm sc}$ (mA cm ⁻²)	$V_{ m oc}$ (V)	FF (%)	PCE (%)
0 h	22.83	1.09	73.63	18.30
120 h	22.74	1.09	73.27	18.11
240 h	22.68	1.08	72.99	17.92
360 h	22.62	1.08	72.77	17.77
480 h	22.52	1.08	72.18	17.52
600 h	22.43	1.07	72.23	17.37

720 h22.261.0771.8717.12840 h22.221.0671.3916.86960 h21.951.0670.5316.401080 h21.851.0669.9416.141200 h21.781.0568.9215.81
960 h 21.95 1.06 70.53 16.40 1080 h 21.85 1.06 69.94 16.14
1080 h 21.85 1.06 69.94 16.14
1200 h 21.78 1.05 68.92 15.81
1320 h 21.75 1.05 67.91 15.48
1440 h 21.64 1.04 66.89 15.10
1560 h 21.61 1.04 66.37 14.87
MD (x=0.05) J_{sc} (mA cm ⁻²) V_{oc} (V) FF (%) PCE (%)
0 h 22.77 1.10 76.74 19.23
120 h 22.73 1.10 76.44 19.12
240 h 22.68 1.10 76.20 19.01
360 h 22.74 1.10 76.01 18.98
480 h 22.48 1.10 75.82 18.68
600 h 22.43 1.09 74.98 18.37
720 h 22.17 1.09 74.61 18.02
720 h 22.17 1.09 74.61 18.02

1200 h	21.86	1.08	72.38	17.02
1320 h	21.95	1.07	72.20	16.99
1440 h	21.85	1.07	71.82	16.79
1560 h	21.65	1.07	71.02	16.42
MD (x=0.10)	$J_{\rm sc}$ (mA cm ⁻²)	$V_{ m oc}$ (V)	FF (%)	PCE (%)
0 h	21.71	1.12	72.57	17.63
120 h	21.61	1.11	72.12	17.24
240 h	21.32	1.10	71.71	16.80
360 h	21.13	1.09	71.10	16.41
480 h	20.83	1.09	70.98	16.07
600 h	20.76	1.08	70.47	15.82
720 h	20.68	1.08	69.62	15.50
840 h	20.63	1.07	69.09	15.23
960 h	20.55	1.06	68.67	14.98
1080 h	20.52	1.06	67.33	14.61
1200 h	20.17	1.05	67.02	14.22
1320 h	19.82	1.05	66.99	13.91
1440 h	19.43	1.04	66.79	13.52
1560 h	18.90	1.04	65.42	12.82

MAPbI ₃	$J_{\rm sc}$ (mA cm ⁻²)	$V_{ m oc}$ (V)	FF (%)	PCE (%)
0	21.48	1.07	71.67	16.53
10	20.89	1.05	70.92	15.57
20	20.35	1.03	69.02	14.49
40	19.77	1.02	68.89	13.89
60	19.39	1.01	68.56	13.44
90	18.95	1.00	68.23	12.94
120	17.64	0.98	67.78	11.73
150	16.78	0.97	65.91	10.68
180	14.35	0.95	63.22	8.58
210	12.67	0.92	61.91	7.23
240	9.98	0.90	56.82	5.11
MD (x=0.03)	$J_{\rm sc}$ (mA cm ⁻²)	$V_{ m oc}$ (V)	FF (%)	PCE (%)
0	22.83	1.09	73.63	18.34
10	22.67	1.09	73.50	18.12
20	22.53	1.08	72.87	17.72
40	22.64	1.08	72.61	17.76

Table S4. Photovoltaic parameters of $[(BE_2PbI_4)_x(FA_{0.9}Cs_{0.1}PbI_3)_{1-x}]_{0.85}(FAPbBr_3)_{0.15}$ (x=0.15, 0.20,0.25) PSCs for heat stability measurements 85 °C.

60	22.41	1.07	72.37	17.54
90	22.27	1.07	72.29	17.27
120	22.00	1.07	71.51	16.81
150	21.87	1.06	70.02	16.26
180	21.74	1.06	69.23	15.90
210	21.29	1.05	68.77	15.36
240	21.22	1.04	67.90	14.82
MD (x=0.05)	$J_{\rm sc}$ (mA cm ⁻²)	$V_{ m oc}$ (V)	FF (%)	PCE (%)
0	22.77	1.10	76.74	19.24
10	22.72	1.10	76.29	19.02
20	22.79	1.09	76.21	18.98
40	22.70	1.09	76.22	18.86
60	22.62	1.09	76.20	18.79
90	22.42	1.09	76.18	18.58
120	22.11	1.08	75.97	18.18
150	21.91	1.08	75.70	17.89
180	21.34	1.07	75.01	17.19
210	21.15	1.07	73.94	16.73
240	21.05	1.07	72.89	16.16

MD (x=0.10)	$J_{\rm sc}$ (mA cm ⁻²)	$V_{ m oc}$ (V)	FF (%)	PCE (%)
0	21.71	1.12	72.57	17.65
10	21.16	1.11	71.70	16.84
20	20.83	1.10	70.71	16.16
40	21.14	1.09	70.84	16.33
60	20.92	1.09	70.09	15.98
90	20.76	1.09	69.91	15.80
120	20.58	1.08	68.99	15.31
150	20.50	1.07	67.99	14.94
180	20.53	1.06	66.89	14.60
210	20.28	1.05	66.21	14.10
240	19.92	1.04	65.58	13.25